

E1
²¹46. (amended) The construction of claim ¹⁸43 wherein the conductive layer is on the first electrode.

²²47. (amended) The construction of claim ¹⁸43 wherein the conductive layer comprises elemental metal, a metal alloy, or a metal containing compound.

²⁵50. (new) The construction of claim ²⁶26 wherein the substrate comprises a semiconductive wafer.

E2
²⁶51. (new) The construction of claim ²⁶26 wherein the first capacitor electrode comprises HSG polysilicon.

²⁷52. (new) The construction of claim ²⁶51, wherein the atomic layer deposited barrier layer comprises TiN and the first capacitor electrode further comprises the TiN.

²⁸53. (new) The construction of claim ²⁶26 wherein the atomic layer deposited barrier layer comprises TiN.

²⁹54. (new) The construction of claim ²⁶26 wherein the capacitor dielectric layer comprises Al₂O₃.

³⁰55. (new) The construction of claim ²⁶26 wherein the second capacitor electrode comprises TiN.

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56. (new) The construction of claim ¹28 wherein the first capacitor electrode comprises HSG polysilicon, the atomic layer deposited barrier layer comprises TiN, the capacitor dielectric layer comprises Al₂O₃, and the second capacitor electrode comprises TiN.

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57. (new) The construction of claim ⁶31 wherein the substrate comprises a semiconductive wafer.

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58. (new) The construction of claim ⁶31 wherein the first capacitor electrode comprises HSG polysilicon.

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59. (new) The construction of claim ³³58, wherein the barrier layer comprises TiN and the first capacitor electrode further comprises the TiN.

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60. (new) The construction of claim ⁶31 wherein the barrier layer comprises TiN.

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61. (new) The construction of claim ⁶31 wherein the capacitor dielectric layer comprises Al₂O₃.

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62. (new) The construction of claim ⁶31 wherein the second capacitor electrode comprises TiN.

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63. (new) The construction of claim ⁶31 wherein the first capacitor electrode comprises HSG polysilicon, the barrier layer comprises TiN, the capacitor dielectric layer comprises Al₂O₃, and the second capacitor electrode comprises TiN.

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64. (new) The construction of claim 38 wherein the substrate comprises a semiconductive wafer.

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65. (new) The construction of claim 38 wherein the first capacitor electrode comprises HSG polysilicon.

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66. (new) The construction of claim 65, wherein the atomic layer deposited conductive layer comprises TiN and the first capacitor electrode further comprises the TiN.

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67. (new) The construction of claim 38 wherein the atomic layer deposited conductive layer comprises TiN.

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68. (new) The construction of claim 38 wherein the capacitor dielectric layer comprises Al_2O_3 .

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69. (new) The construction of claim 38 wherein the second capacitor electrode comprises TiN.

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70. (new) The construction of claim 38 wherein the first capacitor electrode comprises HSG polysilicon, the atomic layer deposited conductive layer comprises TiN, the capacitor dielectric layer comprises Al_2O_3 , and the second capacitor electrode comprises TiN.

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71. (new) The construction of claim 43 wherein the substrate comprises a semiconductive wafer.

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72. (new) The construction of claim ¹⁸43 wherein the first capacitor electrode comprises HSG polysilicon.

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73. (new) The construction of claim ⁴⁸72, wherein the conductive layer comprises TiN and the first capacitor electrode further comprises the TiN.

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74. (new) The construction of claim ¹⁸43 wherein the conductive layer comprises TiN.

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75. (new) The construction of claim ¹⁸43 wherein the capacitor dielectric layer comprises Al₂O₃.

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76. (new) The construction of claim ¹⁸43 wherein the second capacitor electrode comprises TiN.

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77. (new) The construction of claim ¹⁸43 wherein the first capacitor electrode comprises HSG polysilicon, the conductive layer comprises TiN, the capacitor dielectric layer comprises Al₂O₃, and the second capacitor electrode comprises TiN.